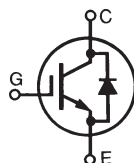


High Voltage, High Gain BIMOSFET™ Monolithic Bipolar MOS Transistor

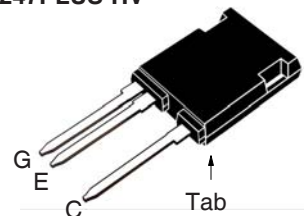
IXBX28N300HV

$$\begin{aligned} V_{CES} &= 3000V \\ I_{C110} &= 28A \\ V_{CE(sat)} &\leq 2.7V \end{aligned}$$



Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	3000	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GE} = 1M\Omega$	3000	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	62	A
I_{C110}	$T_C = 110^\circ\text{C}$	28	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1ms	200	A
SSOA	$V_{GE} = 15V$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 15\Omega$	$I_{CM} = 220$	A
(RBSOA)	Clamped Inductive Load	1500	V
T_{SC} (SCSOA)	$V_{GE} = 15V$, $T_J = 125^\circ\text{C}$, $R_G = 52\Omega$, $V_{CE} = 1250V$, Non-Repetitive	10	μs
P_C	$T_C = 25^\circ\text{C}$	350	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
T_{SOLD}	1.6 mm (0.062 in.) from Case for 10	260	$^\circ\text{C}$
F_C	Mounting Force	20..120/4.5..27	N/lb
Weight		6	g

TO-247PLUS-HV



G = Gate E = Emitter
C = Collector Tab = Collector

Features

- High Blocking Voltage
- High Voltage Package
- Low Conduction Losses

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- Uninterruptible Power Supplies (UPS)
- Switch-Mode and Resonant-Mode Power Supplies
- Capacitor Discharge Circuits
- Laser Generators

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu\text{A}$, $V_{GE} = 0V$	3000		V
$V_{GE(th)}$	$I_C = 250\mu\text{A}$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$, $V_{GE} = 0V$ $T_J = 125^\circ\text{C}$			25 μA 1 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 25V$			± 200 nA
$V_{CE(sat)}$	$I_C = 28A$, $V_{GE} = 15V$, Note 1 $T_J = 125^\circ\text{C}$		2.3 2.8	2.7 V V

Symbol Test Conditions

($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

Min. Typ. Max.

g_{fs}	$I_C = 28\text{A}, V_{CE} = 10\text{V}, \text{Note 1}$	14	24	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		2370	pF
C_{oes}			87	pF
C_{res}			30	pF
$Q_{g(on)}$	$I_C = 28\text{A}, V_{GE} = 15\text{V}, V_{CE} = 1500\text{V}$		110	nC
Q_{ge}			14	nC
Q_{gc}			50	nC
$t_{d(on)}$	Resistive Switching Times, $T_J = 25^\circ\text{C}$ $I_C = 28\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 960\text{V}, R_G = 10\Omega$		50	ns
t_r			412	ns
$t_{d(off)}$			125	ns
t_f			3660	ns
$t_{d(on)}$	Resistive Switching Times, $T_J = 125^\circ\text{C}$ $I_C = 28\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 960\text{V}, R_G = 10\Omega$		74	ns
t_r			805	ns
$t_{d(off)}$			245	ns
t_f			3280	ns
R_{thJC}			0.36	$^\circ\text{C/W}$
R_{thCS}		0.15		$^\circ\text{C/W}$

Reverse Diode

Symbol Test Conditions

($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

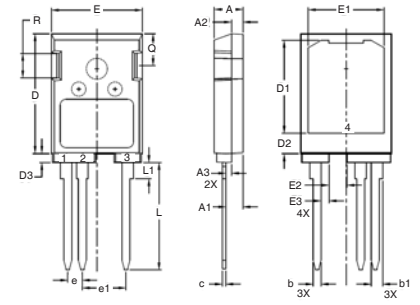
Characteristic Values

Min. Typ. Max

V_F	$I_F = 28\text{A}, V_{GE} = 0\text{V}, \text{Note 1}$		2.7	V
t_{rr}	$I_F = 14\text{A}, V_{GE} = 0\text{V}, -di_F/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GE} = 0\text{V}$		1.5	μs
I_{RM}			31.0	A
Q_{RM}			22.5	μC

Note 1: Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

TO-247PLUS-HV Outline



1 - Gate
2,4 - Emitter
3 - Collector

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.114	.122	2.90	3.10
A2	.075	.083	1.90	2.10
A3	.035	.043	0.90	1.10
b	.053	.059	1.35	1.50
b1	.075	.083	1.90	2.10
c	.022	.030	0.55	0.75
D	.819	.843	20.80	21.40
D1	.638	.646	16.20	16.40
D2	.134	.146	3.40	3.70
D3	.055	.063	1.40	1.60
E	.622	.638	15.80	16.20
E1	.520	.528	13.20	13.40
E2	.118	.126	3.00	3.20
E3	.051	.059	1.30	1.50
e	.100	BSC	2.54	BSC
e1	.300	BSC	7.62	BSC
L	.732	.748	18.60	19.00
L1	.106	.118	2.70	3.00
Q	.216	.224	5.50	5.70
R	.165	.169	4.20	4.30

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

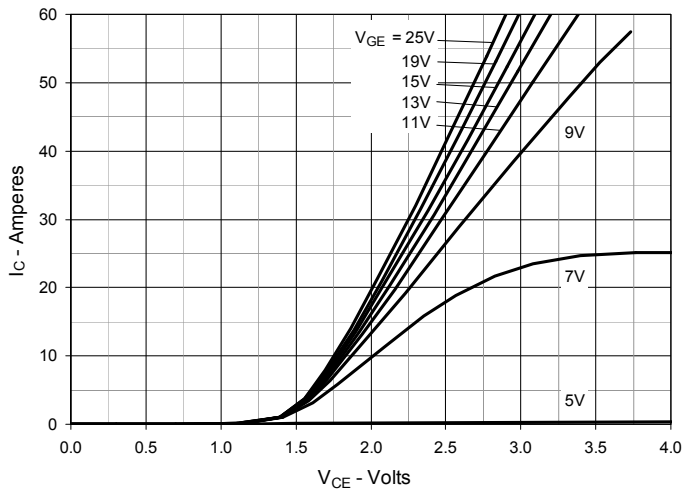
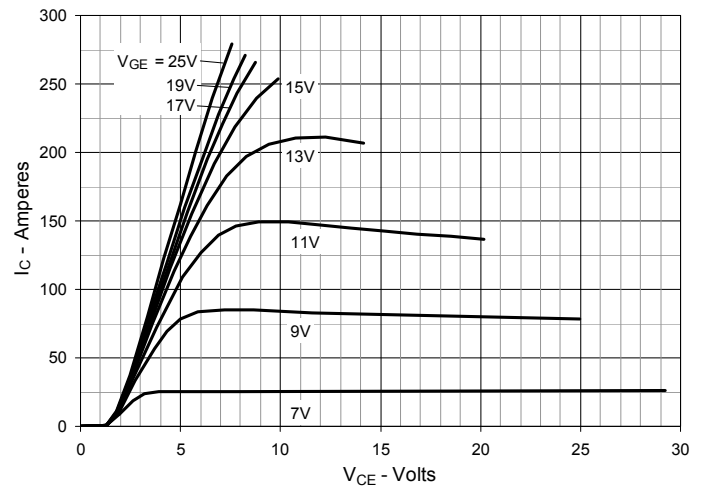
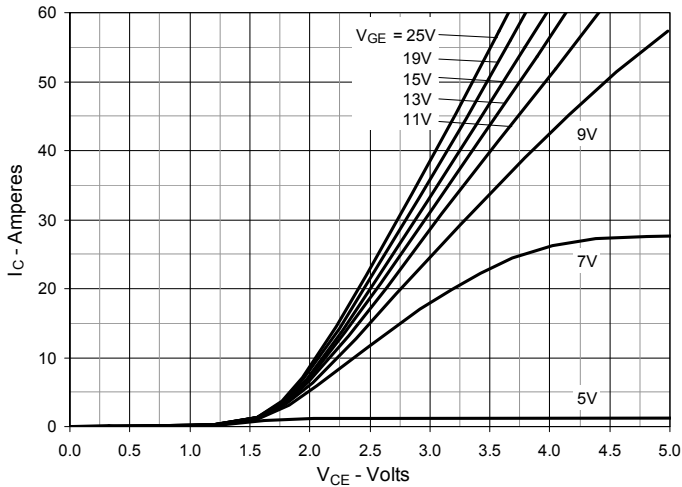
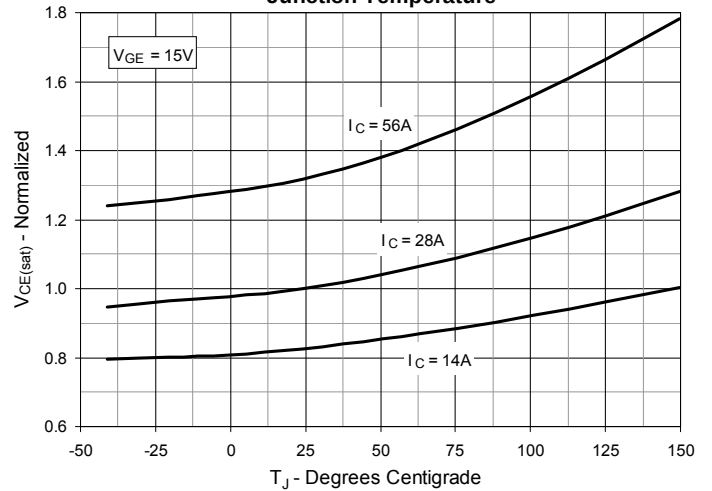
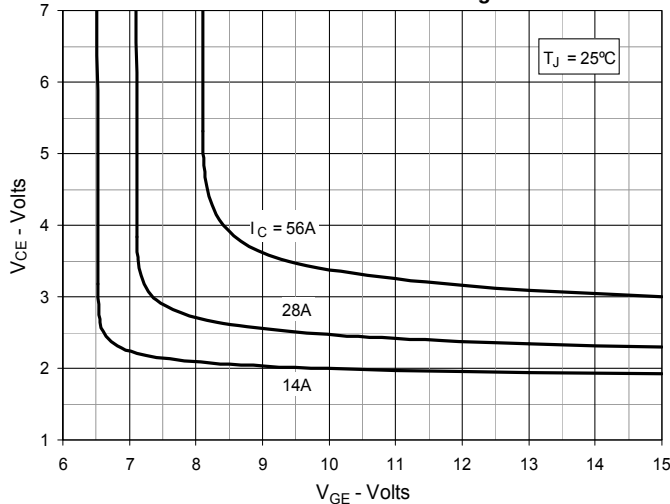
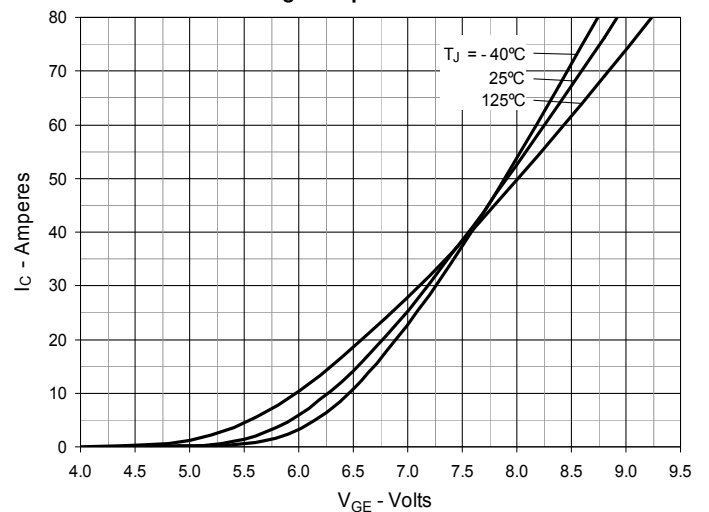
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

Fig. 6. Input Admittance


Fig. 7. Transconductance

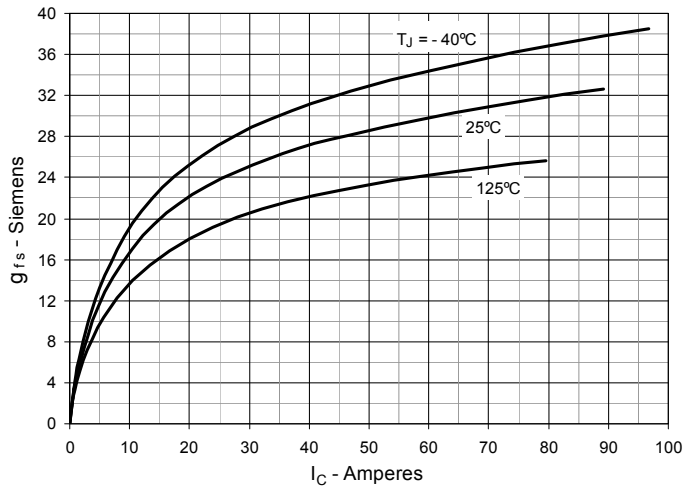


Fig. 8. Gate Charge

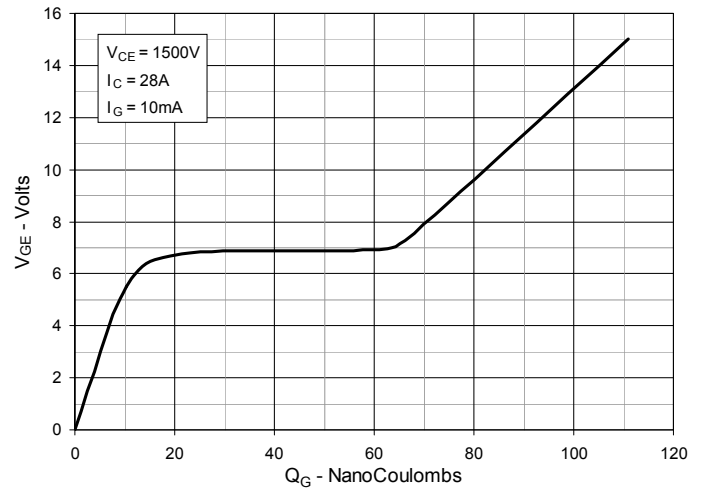


Fig. 9. Forward Voltage Drop of Intrinsic Diode

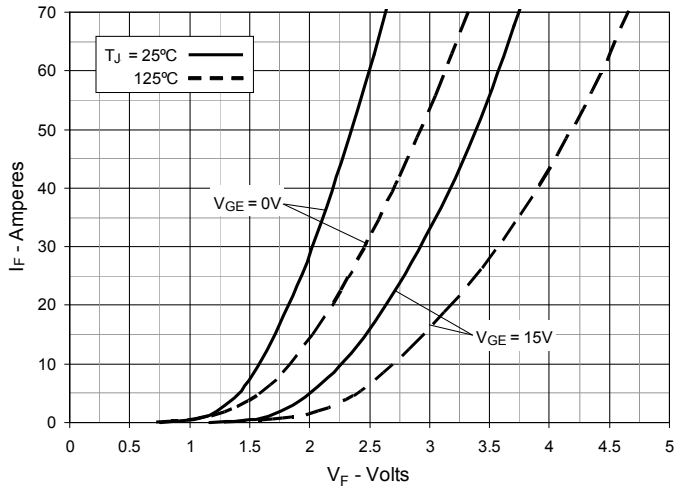


Fig. 10. Capacitance

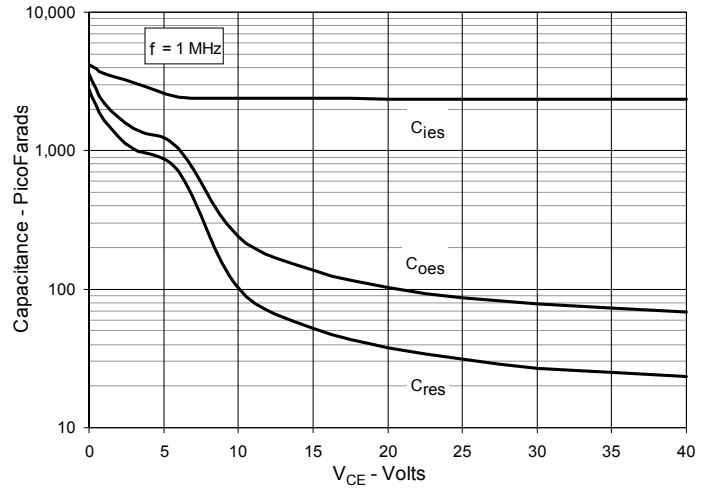


Fig. 11. Reverse-Bias Safe Operating Area

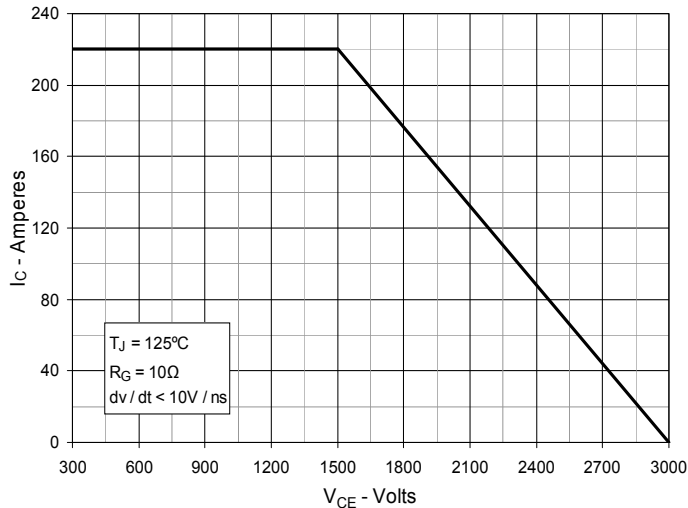


Fig. 12. Maximum Transient Thermal Impedance

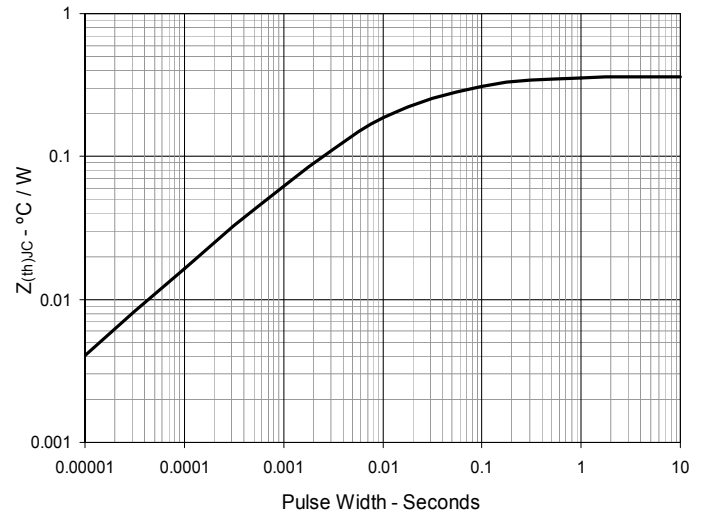


Fig. 13. Forward-Bias Safe Operating Area @ $T_C = 25^\circ\text{C}$

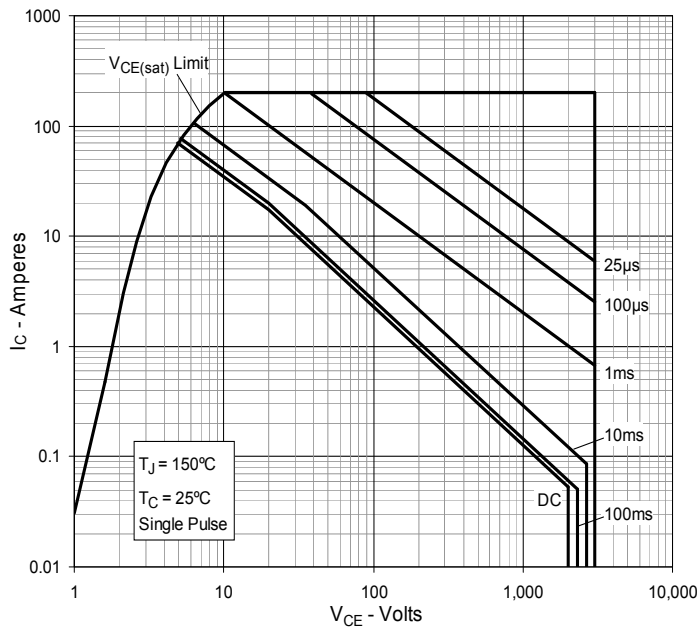
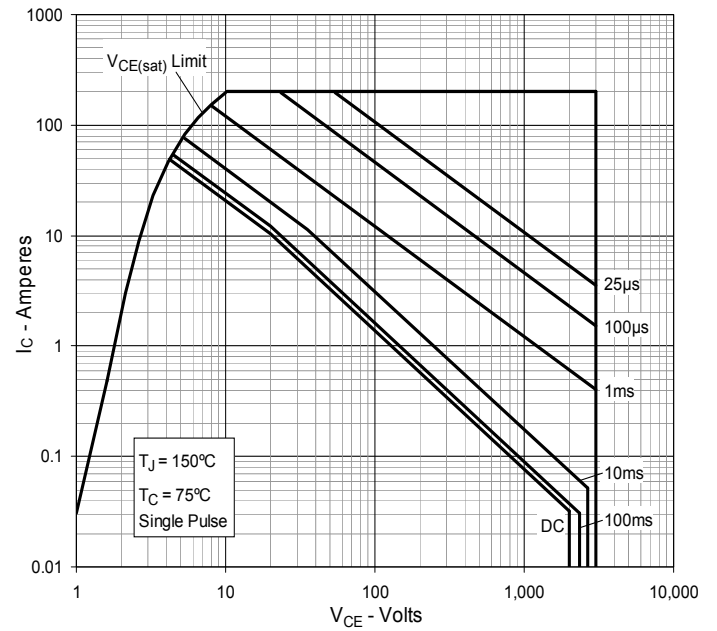


Fig. 14. Forward-Bias Safe Operating Area @ $T_C = 75^\circ\text{C}$





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